

### Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 0.3~2.0GHz
- Typical Pout :  $\geq 34$ dBm(CW)
- Typical Gain: 23dB
- Typical PAE:  $\geq 25\%$
- Bias: 28V@0.3A
- Package: Metal Ceramic

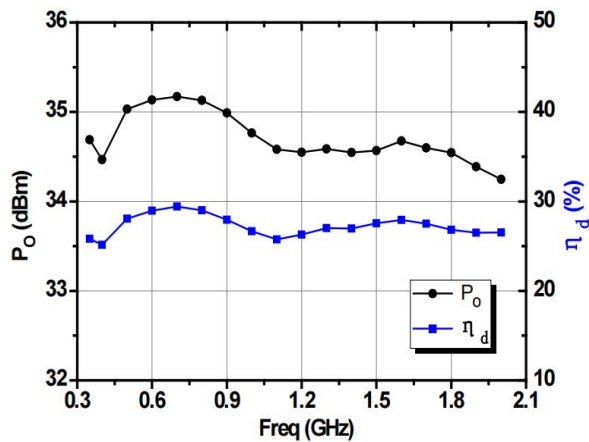


### Electrical Specifications ( $T_A=25^\circ\text{C}, V_d=28\text{V}, I_{dQ}=0.3\text{A}, F: 0.3\sim 2.0\text{GHz}, P_{in}=11\text{dBm}$ )

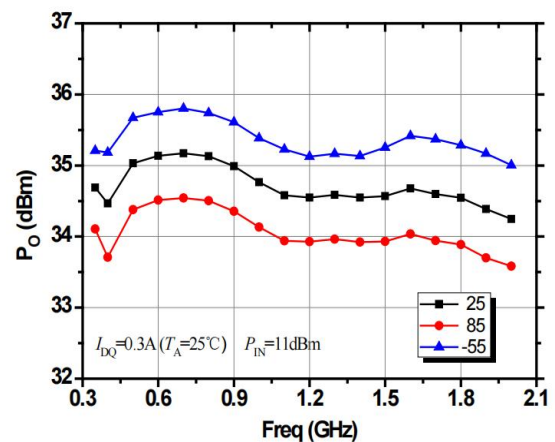
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	34	-	-	dBm
Gp	Power Gain	23	-	-	dB
$\eta_{add}$	Power Added Efficiency	25	-	-	%
$\Delta Gp$	Gain Flatness	-	-	$\pm 0.5$	dB
Rth	Thermal Resistance	-	5	-	$^\circ\text{C/W}$

### Test Curves

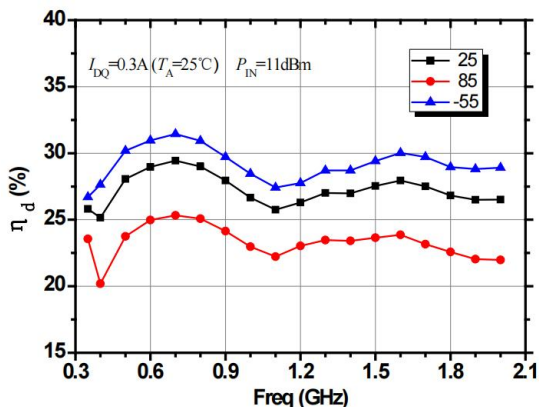
Pout,  $\eta_{add}$ &Freq.



Pout&Freq. @ Different Temp.



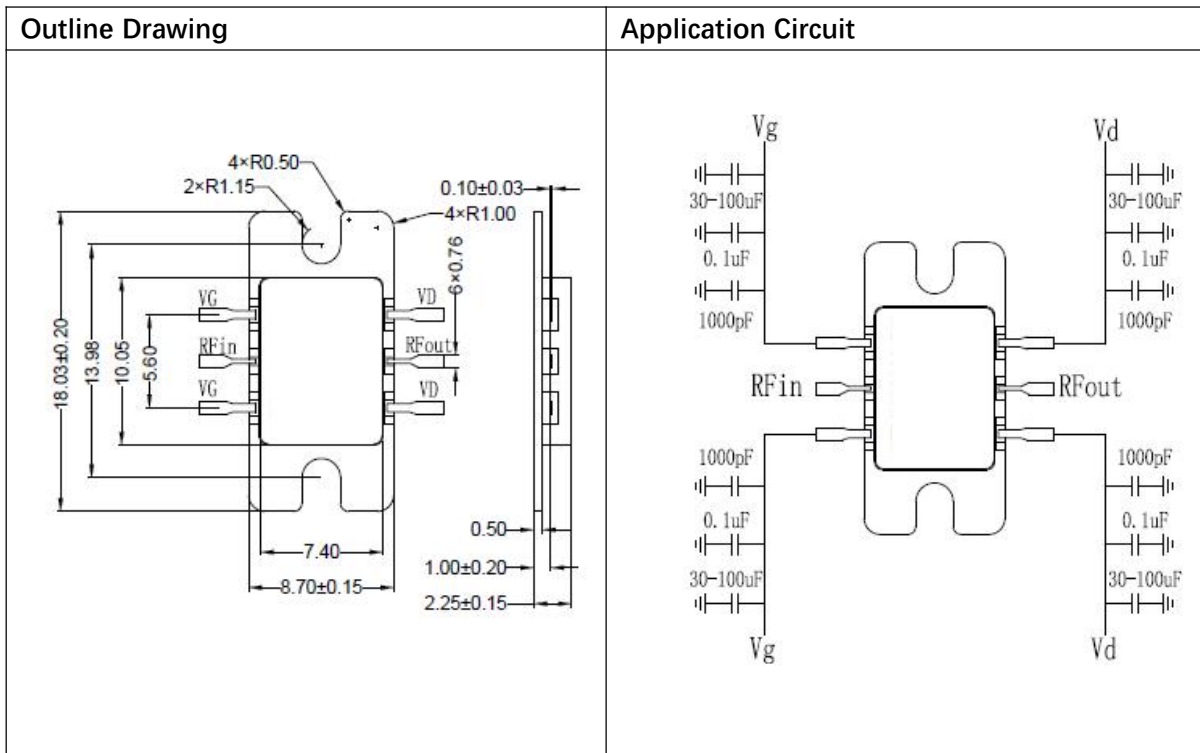
$\eta_{add}$ &Freq. @ Different Temp.



**Absolute Max Ratings (TA=25°C)**

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Pd	DC Dissipation	30W	
Tch	Channel Temperature	150°C	<b>【1】</b>
Tstg	Storage Temperature	-55~85°C	

**【1】 Exceeding any one or combination of these limits may cause permanent damage.**



**Note:**

- (1) The input and output impedance values of this product are both 50 ohms;
- (2) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (3) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (4) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it.